

2W 830nm Single Emitter Bare Laser Bar

Single-emitter laser diode (SE) chips are the basic building block for high-power and high-brightness semiconductor laser modules.

We manufacture single chips with a variety of output powers and wavelengths.



Data Sheet

Item No: LC808SE2

Item Name: 2W 830nm Single-emitter SE Bare Laser Bar

Operation

Center Wavelength	808nm
Output Power	2W
Operation Mode	CW
Power modulation	100%

Geometrical

Emitter width	40um
Cavity length	2000um
Chip Height	150um
Chip width	400um

Electro Optical Data

Threshold current	0.3A
Operating current	2A
Operating voltage	1.8V
Pulse wavelength	808nm
Slope efficiency	1.2W/A
Conversion efficiency	55%
Slow axis divergence	10
Fast axis divergence	35
Spectral width	3nm
Polarization	TE
Temperature characteristics	0.28nm/°C
LD Operating temperature	25°C